Ikuo Suemune

List of Publications by Year
in descending order

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327	5,561	101543	128289
papers	citations	36 h-index	60 g-index

327	327	327	2766
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Microstructures of GaAsN grown on (001) GaAs by metalorganic molecular beam epitaxy. , 2018, , 197-200.		0
2	Optical control of spectral diffusion with single InAs quantum dots in a silver-embedded nanocone. Optics Express, 2017, 25, 8073.	3.4	5
3	Stable and efficient collection of single photons emitted from a semiconductor quantum dot into a single-mode optical fiber. Applied Physics Express, 2016, 9, 032801.	2.4	19
4	Nonlocal biphoton generation in a Werner state from a single semiconductor quantum dot. Physical Review B, 2015, 91, .	3.2	3
5	Optical observation of superconducting density of states in luminescence spectra of InAs quantum dots. Physical Review B, 2015, 92, .	3.2	7
6	Time-resolved measurements of Cooper-pair radiative recombination in InAs quantum dots. Journal of Applied Physics, 2015, 118, 073102.	2.5	1
7	Ultrahigh quality factor in a metal-embedded semiconductor microdisk cavity. Optics Letters, 2015, 40, 5766.	3.3	2
8	Subwavelength metallic cavities with high-Qresonance modes. Nanotechnology, 2015, 26, 085201.	2.6	2
9	Superconducting Light-Emitting Diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2015, 21, 1-11.	2.9	9
10	Vanishing fine-structure splittings in telecommunication-wavelength quantum dots grown on (111)A surfaces by droplet epitaxy. Physical Review B, 2014, 90, .	3.2	41
11	Two-photon interference and coherent control of single InAs quantum dot emissions in an Ag-embedded structure. Journal of Applied Physics, 2014, 116, .	2.5	4
12	Carrier flow and nonequilibrium superconductivity in superconductor-based LEDs. Applied Physics Express, 2014, 7, 073101.	2.4	2
13	Symmetric quantum dots as efficient sources of highly entangled photons: Violation of Bell's inequality without spectral and temporal filtering. Physical Review B, 2013, 88, .	3.2	116
14	Temperature dependent carrier dynamics in telecommunication band InAs quantum dots and dashes grown on InP substrates. Journal of Applied Physics, 2013, 113, .	2.5	37
15	Single-photon emission in telecommunication band from an InAs quantum dot grown on InP with molecular-beam epitaxy. Applied Physics Letters, 2013, 103, .	3.3	29
16	Growth and Optimization of 2-Î¼m InGaSb/AlGaSb Quantum-Well-Based VECSELs on GaAs/AlGaAs DBRs. IEEE Journal of Selected Topics in Quantum Electronics, 2013, 19, 1700611-1700611.	2.9	4
17	Metal-coated semiconductor nanostructures and simulation of photon extraction and coupling to optical fibers for a solid-state single-photon source. Nanotechnology, 2013, 24, 455205.	2.6	15
18	Enhanced light absorption in thin-film solar cells with light propagation direction conversion. Optics Express, 2013, 21, A539.	3.4	7

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19	Carrier dynamics and photoluminescence quenching mechanism of strained InGaSb/AlGaSb quantum wells. Journal of Applied Physics, 2013, 113, 053505.	2.5	5
20	Enhanced Photon Extraction from a Quantum Dot Induced by a Silver Microcolumnar Photon Reflector. Applied Physics Express, 2013, 6, 062801.	2.4	15
21	Fiber-Based Bidirectional Solid-State Single-Photon Emitter Based on Semiconductor Quantum Dot. Applied Physics Express, 2013, 6, 065203.	2.4	15
22	Carrier-transfer dynamics between neutral and charged excitonic states in a single quantum dot probed with second-order photon correlation measurements. Physical Review B, 2013, 88, .	3.2	8
23	Bright single-photon source based on an InAs quantum dot in a silver-embedded nanocone structure. Applied Physics Letters, 2013, 102, 131114.	3.3	20
24	High-Q resonance modes observed in a metallic nanocavity. Applied Physics Letters, 2013, 103, .	3.3	5
25	Spectral and Transient Luminescence Measurements on GaSb/AlGaSb Quantum Wells Grown on GaSb/GaAs Heterojunctions with and without Interfacial Misfit Arrays. Japanese Journal of Applied Physics, 2013, 52, 022101.	1.5	0
26	Silver Embedded Nanomesas as Enhanced Single Quantum Dot Emitters in the Telecommunication C Band. Japanese Journal of Applied Physics, 2012, 51, 06FF12.	1.5	3
27	Longitudinal and transverse exciton-spin relaxation in a single InAsP quantum dot embedded inside a standing InP nanowire using photoluminescence spectroscopy. Physical Review B, 2012, 85, .	3.2	7
28	Anomalous dip observed in intensity autocorrelation function as an inherent nature of single-photon emitters. Applied Physics Letters, 2012, 101, .	3.3	19
29	Photon-pair generation based on superconductivity. IEICE Electronics Express, 2012, 9, 1184-1200.	0.8	4
30	Inter-dot coupling and excitation transfer mechanisms of telecommunication band InAs quantum dots at elevated temperatures. New Journal of Physics, 2012, 14, 023037.	2.9	8
31	Cooper-Pair Radiative Recombination in Semiconductor Heterostructures: Impact on Quantum Optics and Optoelectronics. Japanese Journal of Applied Physics, 2012, 51, 010114.	1.5	3
32	Cooper-Pair Radiative Recombination in Semiconductor Heterostructures: Impact on Quantum Optics and Optoelectronics. Japanese Journal of Applied Physics, 2012, 51, 010114.	1.5	3
33	Silver Embedded Nanomesas as Enhanced Single Quantum Dot Emitters in the Telecommunication C Band. Japanese Journal of Applied Physics, 2012, 51, 06FF12.	1.5	0
34	Characterization of two-photon polarization mixed states generated from entangled-classical hybrid photon source. Optics Express, 2011, 19, 14249.	3.4	5
35	Exploring Spontaneous Simultaneous Photon-pair Generation in Semiconductors. AIP Conference Proceedings, 2011, , .	0.4	0
36	Strongly suppressed multiâ€photon generation from a single quantum dot in a metalâ€embedded structure. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 337-339.	0.8	10

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37	GaSb quantum rings grown by metal organic molecular beam epitaxy. Journal of Crystal Growth, 2011, 323, 233-235.	1.5	1
38	Precise slit-width control of niobium apertures for superconducting LEDs. Nanotechnology, 2011, 22, 045302.	2.6	3
39	Transport Properties of Andreev Polarons in a Superconductor-Semiconductor-Superconductor Junction with Superlattice Structure. Physical Review Letters, 2011, 106, 157002.	7.8	5
40	Enhanced Photon Generation in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>Nb</mml:mi><mml:mo>/</mml:mo><mml:mi>n</mml:mi><mml:mo>â^'</mml:mo><mml:mi>InGaAs</mml:m Light Emitting Device. Physical Review Letters, 2011, 107, 157403.	7.8	43
41	Conversion of Light Propagation Direction for Highly Efficient Solar Cells. Applied Physics Express, 2011, 4, 102301.	2.4	5
42	Superconducting transport in an LED with Nb electrodes. Physica C: Superconductivity and Its Applications, 2010, 470, 814-817.	1.2	7
43	First-order photon interference of a single photon from a single quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2536-2539.	2.7	0
44	Quantum-Dot-Based Photon Emission and Media Conversion for Quantum Information Applications. Advances in Mathematical Physics, 2010, 2010, 1-13.	0.8	7
45	Transport characteristics of a superconductor-based LED. Superconductor Science and Technology, 2010, 23, 034025.	3.5	10
46	Position controlled nanowires for infrared single photon emission. Applied Physics Letters, 2010, 97, .	3.3	55
47	A Cooper-Pair Light-Emitting Diode: Temperature Dependence of Both Quantum Efficiency and Radiative Recombination Lifetime. Applied Physics Express, 2010, 3, 054001.	2.4	21
48	Luminescence of a Cooper Pair. Physical Review Letters, 2009, 103, 187001.	7.8	41
49	LO phononâ€"plasmon coupled modes and carrier mobilities in heavily Se-doped Ga(As, N) thin films. Journal of Materials Science: Materials in Electronics, 2009, 20, 425-429.	2.2	1
50	Spinâ€flip quenching in trion state mediated by optical phonons in a single quantum dot. Physica Status Solidi (B): Basic Research, 2009, 246, 775-778.	1.5	1
51	Improved luminescence efficiency of InAs quantum dots grown on atomic terraced GaAs surface prepared with in-situ chemical etching. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 868-871.	0.8	1
52	Exciton coherence in clean single InP/InAsP/InP nanowire quantum dots emitting in infra-red measured by Fourier spectroscopy. Journal of Physics: Conference Series, 2009, 193, 012132.	0.4	11
53	Fourier spectroscopy of decoherence of exciton and their complexes in single InAlAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 351-355.	0.8	1
54	Luminescence observed from a junction fieldâ€effect transistor with Nb/nâ€InGaAs/Nb junction. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2816-2818.	0.8	6

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55	Response to â€œComment on â€˜Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxyâ€™â€•[J. Crystal Growth 301â€“302 (2007) 277]. Journal of Crystal Growth, 2008, 310, 723.	1.5	1
56	Single photon emission with high degree of circular polarization from a single quantum dot under zero magnetic field. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1824-1827.	2.7	2
57	Highly circular-polarized single photon generation from a single quantum dot at zero magnetic field. Microelectronics Journal, 2008, 39, 327-330.	2.0	1
58	Role of Cooper pairs for the generation of entangled photon pairs from single quantum dots. Microelectronics Journal, 2008, 39, 344-347.	2.0	5
59	Electron effective mass and mobility in heavily doped n-GaAsN probed by Raman scattering. Journal of Applied Physics, 2008, 103, 103528.	2.5	17
60	Superconductor-based Light Emitting Diode: Demonstration of Role of Cooper Pairs in Radiative Recombination Processes. Applied Physics Express, 2008, 1, 011701.	2.4	29
61	Exciton-phonon interactions observed in blue emission band in Te-delta-doped ZnSe. Journal of Applied Physics, 2008, 104, 033531.	2.5	2
62	Superconducting Effect on Radiative Recombinations in Long-wavelength Light Emitting Diode. , 2008, , .		0
63	Superconducting photonics and development of light emitting diodes based on new concept. , 2008, , .		0
64	Excitonic spin-state preservation mediated by optical-phonon resonant excitation in a single quantum dot. Physical Review B, 2008, 78, .	3.2	4
65	Differential resistance oscillations with microwave irradiation in a superconductor-semiconductor junction. Journal of Physics: Conference Series, 2008, 109, 012033.	0.4	4
66	Nucleation and Growth Mode of GaN on Vicinal SiC Surfaces. Japanese Journal of Applied Physics, 2007, 46, L348-L351.	1.5	1
67	Novel Nano-Heterostructure Materials and Related Devices. , 2007, , 281-327.		0
68	Fabrication and characterization of a highQmicrodisc laser using InAs quantum dot active regions. Nanotechnology, 2007, 18, 055401.	2.6	3
69	Fundamental Properties of Wide Bandgap Semiconductors. , 2007, , 25-96.		0
70	Room-temperature stimulated emission from ZnO thin films grown by radio-frequency magnetron sputtering. Journal of Luminescence, 2007, 122-123, 825-827.	3.1	4
71	Room temperature ultraviolet lasing action in high-quality ZnO thin films. Journal of Luminescence, 2007, 122-123, 828-830.	3.1	14
72	Luminescence study on evolution from Te isoelectronic centers to type-II ZnTe quantum dots grown by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2007, 301-302, 277-280.	1.5	13

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73	Detailed Measurements of Nuclear Spin Polarizations in a Single InAlAs Quantum Dot Through Overhauser Shift of Photoluminescence. Journal of Superconductivity and Novel Magnetism, 2007, 20, 447-451.	1.8	1
74	Intrinsic exciton transitions in high-quality ZnO thin films grown by plasma-enhanced molecular-beam epitaxy on sapphire substrates. Journal of Applied Physics, 2006, 99, 063709.	2.5	9
75	Formation of CdO dots on atomically flat ZnO surfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 933-937.	0.8	7
76	Origin of asymmetric splitting of a neutral exciton in a single semiconductor quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 3908-3911.	0.8	0
77	Overhauser shift in photoluminescence of excitons with fine structure from a single self-assembled InAlAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4372-4375.	0.8	3
78	Time-resolved photoluminescence in annealed self-assembled InAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 4299-4302.	0.8	0
79	Triggered single-photon emission and cross-correlation properties in InAlAs quantum dot. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 32, 144-147.	2.7	9
80	Role of Nitrogen Precursor Supplies on InAs Quantum Dot Surfaces in Their Emission Wavelengths. Japanese Journal of Applied Physics, 2006, 45, L529-L532.	1.5	3
81	Anisotropic Lattice Deformation of InAs Self-Assembled Quantum Dots Embedded in GaNAs Strain Compensating Layers. Japanese Journal of Applied Physics, 2006, 45, L57-L59.	1.5	3
82	Superconductor-Based Quantum-Dot Light-Emitting Diodes: Role of Cooper Pairs in Generating Entangled Photon Pairs. Japanese Journal of Applied Physics, 2006, 45, 9264-9271.	1.5	38
83	The application of an InGaAsâˆ•GaAsN strain-compensated superlattice to InAs quantum dots. Journal of Applied Physics, 2006, 99, 103103.	2.5	8
84	Deterministic Single-Photon and Polarization-Correlated Photon Pair Generations From a Single InAlAs Quantum Dot. Journal of Nanoelectronics and Optoelectronics, 2006, 1, 39-51.	0.5	35
85	Single-photon generation from InAlAs single quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3833-3837.	0.8	6
86	Dynamic nuclear polarization in a self-assembled InAlAs quantum dot. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3838-3842.	0.8	2
87	Photon Antibunching Observed from an InAlAs Single Quantum Dot. Japanese Journal of Applied Physics, 2005, 44, L793-L796.	1.5	24
88	Nucleation Stages of Carbon Nanotubes on SiC(0001) by Surface Decomposition. Japanese Journal of Applied Physics, 2005, 44, L803-L805.	1.5	12
89	Photon-spin qubit-conversion based on Overhauser shift of Zeeman energies in quantum dots. Applied Physics Letters, 2005, 87, 112506.	3.3	23
90	Structural and Luminescence Properties of InAs Quantum Dots: Effect of Nitrogen Exposure on Dot Surfaces. Japanese Journal of Applied Physics, 2005, 44, L1512-L1515.	1.5	6

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91	Theory of strain states in InAs quantum dots and dependence on their capping layers. Journal of Applied Physics, 2005, 98, 063502.	2.5	22
92	MOMBE Growth and Characterization of IIIâ€“V-N Compounds and Application to InAs Quantum Dots. , 2005, , 137-155.		0
93	Surface-emitting stimulated emission in high-quality ZnO thin films. Journal of Applied Physics, 2004, 96, 3733-3736.	2.5	32
94	SiC Surface Nanostructures Induced by Self-Ordering of Nano-Facets. Materials Science Forum, 2004, 457-460, 407-410.	0.3	1
95	Optical properties of GaAsNSe/GaAs superlattice investigated by means of piezoelectric photothermal spectroscopy for nonradiative electron transitions. IEE Proceedings: Optoelectronics, 2004, 151, 328-330.	0.8	0
96	Dynamical properties of atom-like emissions from single localized states in ZnCdS ternary mesa-shaped structures. Physica Status Solidi (B): Basic Research, 2004, 241, 503-506.	1.5	0
97	Formation of ohmic contacts top-type ZnO. Physica Status Solidi (B): Basic Research, 2004, 241, 635-639.	1.5	10
98	Epitaxial ZnO growth and p-type doping with MOMBE. Physica Status Solidi (B): Basic Research, 2004, 241, 640-647.	1.5	24
99	Study of optimal coupling of ZnS pyramidal microcavities with distributed Bragg reflectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1034-1037.	0.8	0
100	Observation of reflection high-energy electron diffraction oscillation during MOMBE growth of AlAs and related modulated semiconductor structures. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 756-760.	2.7	1
101	Observation of clear negative differential resistance characteristics in GaAsNSe/GaAs and GaAsNSb/GaAs multiple quantum wells at room temperature. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 727-731.	2.7	5
102	IIIâ€“Vâ€“N-related quantum structures for 1.5â€…[micro sign]m emission. IEE Proceedings: Optoelectronics, 2003, 150, 52.	0.8	0
103	IIâ€“VI quantum dots grown by MOVPE. Journal of Crystal Growth, 2003, 248, 301-309.	1.5	9
104	Structural properties of CdO layers grown on GaAs (001) substrates by metalorganic molecular beam epitaxy. Journal of Crystal Growth, 2003, 252, 219-225.	1.5	4
105	Emissions from single localized states observed in ZnCdS ternary alloy mesa structures. Applied Physics Letters, 2003, 82, 4277-4279.	3.3	4
106	Improvement of InAs quantum-dot optical properties by strain compensation with GaNAs capping layers. Applied Physics Letters, 2003, 83, 4524-4526.	3.3	28
107	1.55 Î¼m emission from GaInNAs with indium-induced increase of N concentration. Applied Physics Letters, 2003, 83, 1992-1994.	3.3	12
108	Observation of reflection high-energy electron diffraction oscillation during metalorganic-molecular-beam epitaxy of AlAs and control of carbon incorporation. Journal of Applied Physics, 2003, 94, 4871.	2.5	6

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109	Structural anisotropy in GaN films grown on vicinal 4H-SiC surfaces by metallorganic molecular-beam epitaxy. Applied Physics Letters, 2003, 83, 1569-1571.	3.3	13
110	Self-Ordering of Nanofacets on Vicinal SiC Surfaces. Physical Review Letters, 2003, 91, 226107.	7.8	89
111	Metalorganic molecular-beam epitaxy and characterization of GaAsNSe/GaAs superlattices emitting around 1.5-Î¼m-wavelength region. Applied Physics Letters, 2003, 82, 898-900.	3.3	7
112	GaNAs as Strain Compensating Layer for 1.55 Âµm Light Emission from InAs Quantum Dots. Japanese Journal of Applied Physics, 2003, 42, 5598-5601.	1.5	24
113	Longitudinal-optical-phonon-assisted energy relaxation in self-assembled CdS quantum dots embedded in ZnSe. Journal of Applied Physics, 2002, 92, 3573-3578.	2.5	4
114	Photoluminescence study of InAs quantum dots embedded in GaNAs strain compensating layer grown by metalorganic-molecular-beam epitaxy. Journal of Applied Physics, 2002, 92, 6813-6818.	2.5	36
115	Metalorganic Molecular-Beam Epitaxial Growth and Optical Properties of Er-Doped GaNP. Japanese Journal of Applied Physics, 2002, 41, 1030-1033.	1.5	1
116	H2O-Vapor-Activated ZnO Growth on a-Face Sapphire Substrates by Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, 2851-2854.	1.5	23
117	Growth and structural characterization of IIIÂNÂV semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 755-761.	2.0	36
118	Nitrogen-Doped p-Type ZnO Layers Prepared with H2O Vapor-Assisted Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 2002, 41, L1281-L1284.	1.5	118
119	Longitudinal-Optical-Phonon-Assisted Resonant Excitations of CdS Quantum Dots Embedded in ZnSe/(ZnSe-MgS Superlattice) Microcavities. Physica Status Solidi (B): Basic Research, 2002, 229, 961-969.	1.5	3
120	Study of Resonance Wavelengths in II-VI Semiconductor Photonic Dots: Pyramidal Size Dependences and Luminescence Properties. Physica Status Solidi (B): Basic Research, 2002, 229, 971-976.	1.5	8
121	Growth Activation of ZnO Layers with H2O Vapor ona-Face of Sapphire Substrate by Metalorganic Molecular-Beam Epitaxy. Physica Status Solidi A, 2002, 192, 224-229.	1.7	6
122	Strong coupling of CdS quantum dots to confined photonic modes in ZnSe-based microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 403-407.	2.7	2
123	Modified spontaneous emission properties of CdS quantum dots embedded in novel three-dimensional microcavities. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 13, 441-445.	2.7	6
124	CdO epitaxial layers grown on (001) GaAs surfaces by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2002, 237-239, 518-522.	1.5	15
125	Erbium-doped GaP grown by MOMBE and their optical properties. Journal of Crystal Growth, 2002, 237-239, 1423-1427.	1.5	0
126	Nucleation and growth kinetics of AlN films on atomically smooth 6Hâ€“SiC (0001) surfaces. Applied Physics Letters, 2001, 78, 3612-3614.	3.3	46

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127	Single-crystalline rocksalt CdO layers grown on GaAs (001) substrates by metalorganic molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 470-472.	3.3	27
128	Structural properties of GaAsN grown on (001) GaAs by metalorganic molecular beam epitaxy. Journal of Electronic Materials, 2001, 30, 900-906.	2.2	3
129	RADIATIVE EFFICIENCY OF LOCALIZED EXCITONS IN ZnCdS TERNARY ALLOYS. International Journal of Modern Physics B, 2001, 15, 3718-3721.	2.0	3
130	Selective Growth of Highly Packed Array of ZnCdS Quantum Dots with a Mask Prepared by Atomic Force Microscope Nanolithography. Japanese Journal of Applied Physics, 2001, 40, 1899-1901.	1.5	1
131	Highly conductive GaAsNSe alloys grown on GaAs and their nonalloyed ohmic properties. Applied Physics Letters, 2001, 79, 3284-3286.	3.3	20
132	Luminescence properties of CdS quantum dots embedded in monolithic II-VI microcavity. Springer Proceedings in Physics, 2001, , 675-676.	0.2	0
133	New type of ZnCdS/ZnMgCdS heterostructures lattice-matched to GaAs for selective-area growth. Journal of Crystal Growth, 2000, 214-215, 125-129.	1.5	3
134	Luminescence properties of ZnO films grown on GaAs substrates by molecular-beam epitaxy excited by electronâ€“cyclotron resonance oxygen plasma. Journal of Crystal Growth, 2000, 214-215, 280-283.	1.5	44
135	Periodic doping of GaAs:Zn p-type nano-clusters in ZnSe grown by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2000, 214-215, 524-528.	1.5	3
136	Study of site change of Li impurities in ZnSe by co-doping with iodine. Journal of Crystal Growth, 2000, 214-215, 562-566.	1.5	7
137	MOVPE growth of ZnSe/ZnMgS distributed Bragg reflectors with high refractive-index contrast. Journal of Crystal Growth, 2000, 214-215, 1019-1023.	1.5	9
138	Enhancement of spontaneous emission by ZnS-based IIâ€“VI semiconductor photonic dots. Journal of Crystal Growth, 2000, 214-215, 1024-1028.	1.5	1
139	Growth mechanism of selectively grown IIâ€“VI semiconductor photonic dots for short-wavelength light emitters. Journal of Crystal Growth, 2000, 221, 425-430.	1.5	8
140	Role of ZnS buffer layers in growth of zincblende ZnO on GaAs substrates by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2000, 221, 435-439.	1.5	42
141	Formation of wire-like surfaces and lateral composition modulation in GaAsN grown by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 2000, 221, 546-550.	1.5	13
142	Microcavities with distributed Bragg reflectors based on ZnSe/MgS superlattice grown by MOVPE. Journal of Crystal Growth, 2000, 221, 699-703.	1.5	26
143	Investigations of optical and electrical properties of In-doped GaN films grown by gas-source molecular beam epitaxy. Journal of Crystal Growth, 2000, 209, 396-400.	1.5	7
144	Fabrication of selectively grown IIâ€“VI widegap semiconductor photonic dots on (001)GaAs with MOMBE. Journal of Crystal Growth, 2000, 209, 518-521.	1.5	3

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145	Origin of size distributions in ZnSe self-organized quantum dots grown on ZnS layers. Journal of Electronic Materials, 2000, 29, 515-519.	2.2	0
146	Intrinsic and Extrinsic Excitonic Features in MgS/ZnSe Superlattices Revealed by Microspectroscopy. Japanese Journal of Applied Physics, 2000, 39, 501-504.	1.5	2
147	Atomic force microscope based patterning of carbonaceous masks for selective area growth on semiconductor surfaces. Journal of Applied Physics, 2000, 88, 3158-3165.	2.5	12
148	Hole activation from GaAs:Zn nanoclusters for p-type conduction in ZnSe. Applied Physics Letters, 2000, 76, 1701-1703.	3.3	2
149	Growth and characterization of hypothetical zinc-blende ZnO films on GaAs(001) substrates with ZnS buffer layers. Applied Physics Letters, 2000, 76, 550-552.	3.3	188
150	Temperature dependence of band gap energies of GaAsN alloys. Applied Physics Letters, 2000, 76, 1285-1287.	3.3	107
151	Role of nitrogen in the reduced temperature dependence of band-gap energy in GaNAs. Applied Physics Letters, 2000, 77, 3021-3023.	3.3	118
152	Nucleation and Faceting in Selectively Grown ZnS Pyramidal Dot Array for Short-Wavelength Light Emitters. Japanese Journal of Applied Physics, 1999, 38, L710-L713.	1.5	10
153	Nucleation in the Nanometer Scale Selective Area Growth of II-VI Semiconductors. Japanese Journal of Applied Physics, 1999, 38, L563-L566.	1.5	1
154	Semiconductor photonic dots: Visible wavelength-sized optical resonators. Applied Physics Letters, 1999, 74, 1963-1965.	3.3	22
155	Growth and luminescence properties of self-organized ZnSe quantum dots. Applied Physics Letters, 1999, 75, 235-237.	3.3	44
156	Role of Indium on Nitrogen Incorporation in GaNAs Grown by Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1309-L1311.	1.5	5
157	Strain effect on the N composition dependence of GaNAs bandgap energy grown on (001) GaAs by metalorganic molecular beam epitaxy. Journal of Crystal Growth, 1999, 201-202, 355-358.	1.5	22
158	GaN Quantum Structures with Fractional Dimension â€" From Quantum Well to Quantum Dot. Physica Status Solidi (B): Basic Research, 1999, 216, 431-434.	1.5	18
159	Reexamination of N composition dependence of coherently grown GaNAs band gap energy with high-resolution x-ray diffraction mapping measurements. Applied Physics Letters, 1999, 74, 1254-1256.	3.3	244
160	Effect of indium doping on the transient optical properties of GaN films. Applied Physics Letters, 1999, 75, 2879-2881.	3.3	40
161	Band gap energy of GaNAs grown on GaAs(001) substrates by metalorganic molecular-beam epitaxy. Journal of Crystal Growth, 1998, 188, 103-106.	1.5	3
162	Metalorganic molecular beam epitaxy of GaNAs alloys on (001)GaAs. Journal of Crystal Growth, 1998, 189-190, 490-495.	1.5	33

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163	MOVPE growth of ZnSe/ZnS distributed Bragg reflectors on GaAs (1 0 0) and (3 1 1)B substrates. Journal of Crystal Growth, 1998, 184-185, 777-782.	1.5	10
164	Atomic force microscope lithography on carbonaceous films deposited by electron-beam irradiation. Applied Physics Letters, 1998, 72, 716-718.	3.3	16
165	Low-Temperature Selective Growth of ZnSe and ZnS on (001) GaAs Patterned with Carbonaceous Mask by Metalorganic Molecular-Beam Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L272-L274.	1.5	13
166	p-type conductivity control of ZnSe with insertion of ZnTe:Li submonolayers in metalorganic molecular-beam epitaxy. Journal of Applied Physics, 1998, 84, 6100-6104.	2.5	6
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